

Abstract of the Disclosure:

A method for the sublimation growth of an SiC single crystal, involving heating up under growth pressure, is described. In the method for the sublimation growth of the SiC single
5 crystal, a crucible holding a stock of solid SiC and an SiC seed crystal, onto which the SiC single crystal grows, is evacuated during a starting phase which precedes the actual growth phase and is then filled with an inert gas, until a growth pressure is reached in the crucible. Moreover, the
10 crucible is initially heated to an intermediate temperature and then, in a heat-up phase, is heated to a growth temperature at a heat-up rate of at most 20° C/min. As a result, controlled seeding on the SiC seed crystal is achieved even during the heat-up phase.

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